

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1444

DESCRIPTION

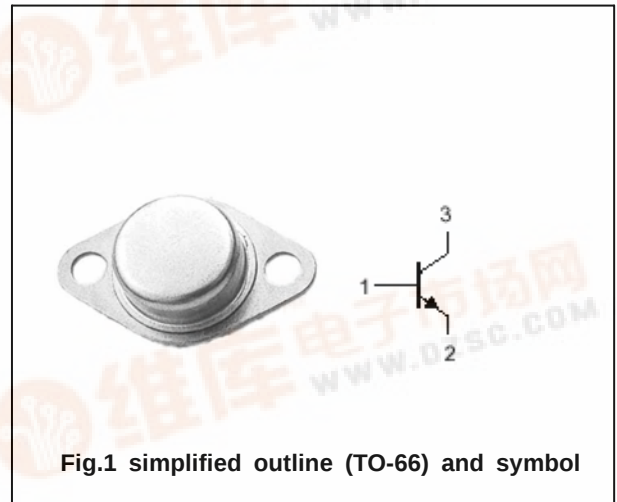
- With TO-66 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For switching and wide-band amplifier applications.

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	80	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_B	Base current		1	A
P_D	Total power dissipation	$T_C = 25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	$I_C=30mA ; I_B=0$	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A ; I_B=1A$			1.5	V
V_{BE}	Base-emitter on voltage	$I_C=6A ; V_{CE}=4V$			2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=80V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=1A ; V_{CE}=4V$	30			
h_{FE-2}	DC current gain	$I_C=3A ; V_{CE}=4V$	15			
f_T	Transition frequency	$I_C=0.5A ; V_{CE}=10V$		10		MHz

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PACKAGE OUTLINE

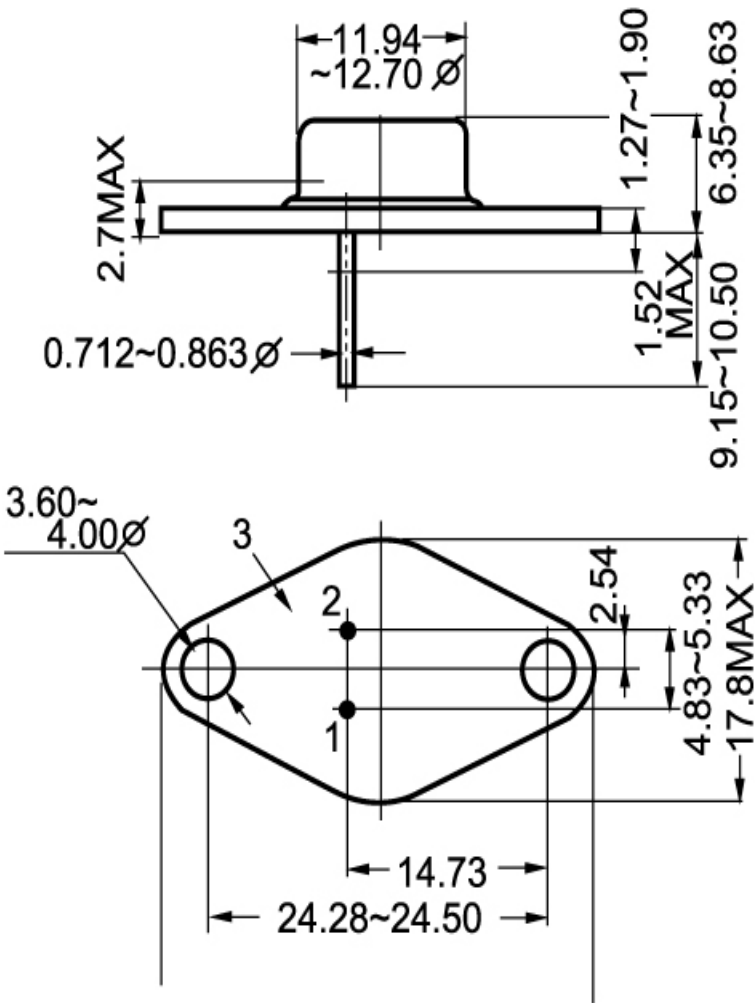


Fig.2 outline dimensions